

**1. Material** Substrate GaAs (P Type)  
Epitaxial Layer GaAs (N/P Type)

**2. Electrode** N(Cathode) Side Gold Alloy  
P(Anode) Side Gold Alloy (Au/Sn Eutectic Metal)

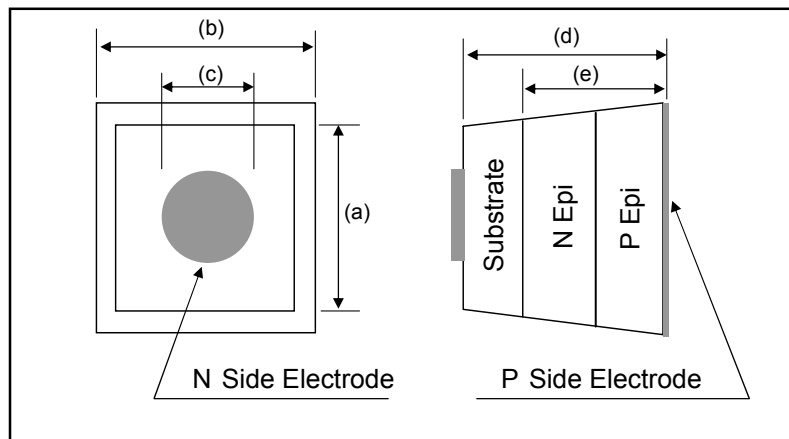
**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_F$		1.25	1.4	V	IF=30mA
Reverse Voltage	$V_R$	8			V	IR=10uA
Power	$P_O$	9.0	11.5		mW	IF=100mA
Wavelength	$\lambda_P$		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data**

- (a) Emission Area ----- 14mil x 14mil
- (b) Bottom Area ----- 15mil x 15mil
- (c) Bonding Pad ----- 130um
- (d) Chip Thickness ----- 8.2mil
- (e) Junction Height ----- 1.1mil



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